

PRODUCT FEATURES

- ☐ IGBT³ CHIP(Trench+Field Stop technology)
- ☐ High short circuit capability,self limiting short circuit current
- ☐ $V_{CE(sat)}$ with positive temperature coefficient
- ☐ Fast switching and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery
- ☐ Low switching losses



APPLICATIONS

- ☐ High frequency switching application
- ☐ Medical applications
- ☐ Motion/servo control
- ☐ UPS systems

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

 $T_C = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J = 25^{\circ}\text{C}$	600	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C = 25^{\circ}\text{C}$	125	A
		$T_C = 70^{\circ}\text{C}$	100	
I_{CM}	Repetitive Peak Collector Current	$t_p = 1\text{ms}$	200	
P_{tot}	Power Dissipation Per IGBT		330	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS

 $T_C = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J = 25^{\circ}\text{C}$	600	V
$I_{F(AV)}$	Average Forward Current	$T_C = 25^{\circ}\text{C}$	100	A
I_{FRM}	Repetitive Peak Forward Current	$t_p = 1\text{ms}$	200	
I^2t		$T_J = 125^{\circ}\text{C}$, $t = 10\text{ms}$, $V_R = 0\text{V}$	1000	A^2S

IGBT-inverter

ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit	
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =1.6mA	4.9	5.8	6.5	V	
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =100A, V _{GE} =15V, T _J =25℃		1.45	1.9		
		I _C =100A, V _{GE} =15V, T _J =125℃		1.6			
I _{CES}	Collector Leakage Current	V _{CE} =600V, V _{GE} =0V, T _J =25℃			1	mA	
		V _{CE} =600V, V _{GE} =0V, T _J =125℃			5	mA	
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±15V, T _J =25℃	-400		400	nA	
R _{gint}	Integrated Gate Resistor			2		Ω	
Q _g	Gate Charge	V _{CE} =300V, I _C =100A , V _{GE} =±15V		1.1		μC	
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =1MHz		6.2		nF	
C _{res}	Reverse Transfer Capacitance			190		pF	
t _{d(on)}	Turn on Delay Time	V _{CC} =300V,I _C =100A R _G =3.3Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	70		ns	
			T _J =125℃	80		ns	
t _r	Rise Time		T _J =25℃	20		ns	
			T _J =125℃	20		ns	
t _{d(off)}	Turn off Delay Time		T _J =25℃	260		ns	
			T _J =125℃	290		ns	
t _f	Fall Time		T _J =25℃	70		ns	
			T _J =125℃	70		ns	
E _{on}	Turn on Energy	V _{CC} =300V,I _C =100A R _G =3.3Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	0.3		mJ	
			T _J =125℃	0.7		mJ	
E _{off}	Turn off Energy		T _J =25℃	2.5		mJ	
			T _J =125℃	3.35		mJ	
I _{sc}	Short Circuit Current		tpsc≤6μS , V _{GE} =15V T _J =125℃,V _{CC} =360V		500		A
R _{thJC}	Junction to Case Thermal Resistance （ Per IGBT ）				0.45	K /W	

Diode-inverter

ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _F	Forward Voltage	I _F =100A , V _{GE} =0V, T _J =25℃		1.55	1.95	V
		I _F =100A , V _{GE} =0V, T _J =125℃		1.50		
t _{rr}	Reverse Recovery Time	I _F =100A , V _R =300V dI _F /dt=-5100A/μs T _J =125℃		130		ns
I _{RRM}	Max. Reverse Recovery Current			150		A
Q _{RR}	Reverse Recovery Charge			8		μC
E _{rec}	Reverse Recovery Energy			2.25		mJ
R _{thJCD}	Junction to Case Thermal Resistance （ Per Diode ）				0.8	K /W

MODULE CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	$^\circ\text{C}$
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		> 200	
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M5)	2.5~5	Nm
Weight			160	g

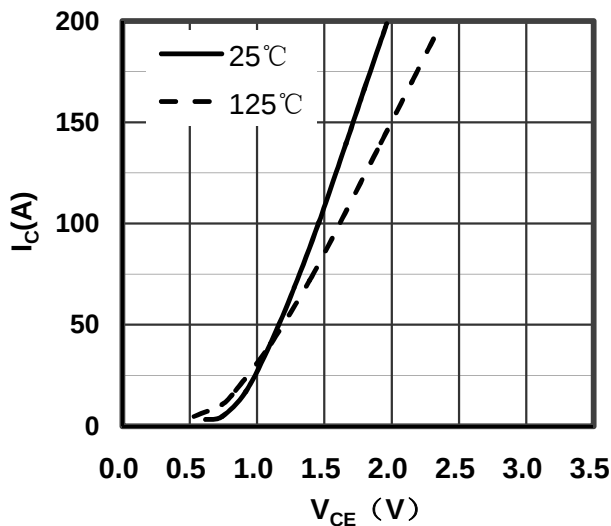


Figure 1. Typical Output Characteristics IGBT-inverter

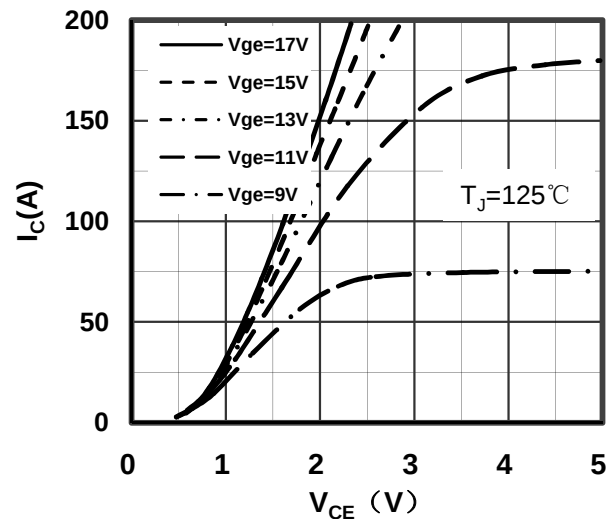


Figure 2. Typical Output Characteristics IGBT-inverter

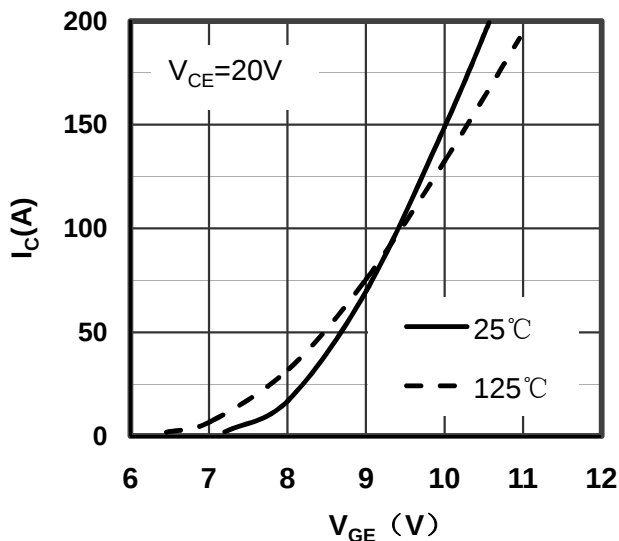


Figure 3. Typical Transfer characteristics IGBT-inverter

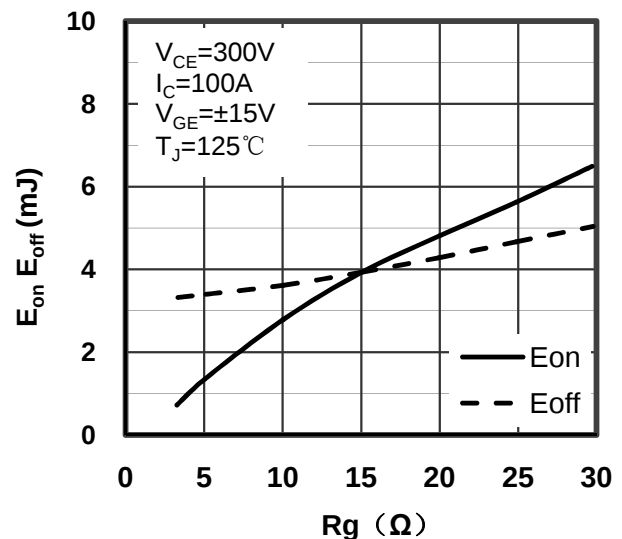


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

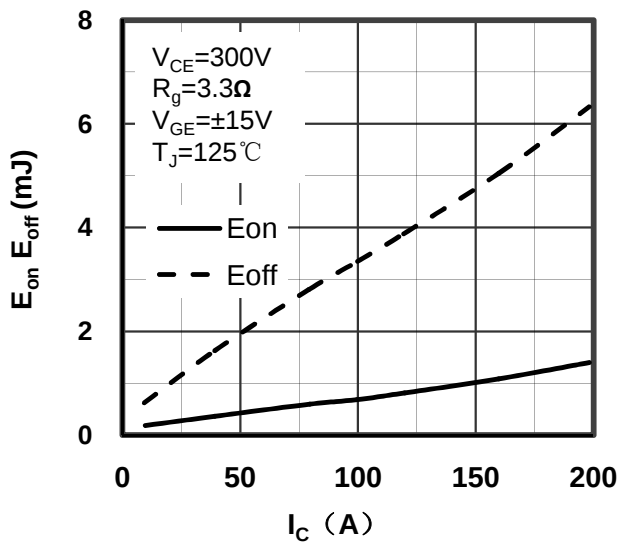


Figure 5. Switching Energy vs Collector Current IGBT-inverter

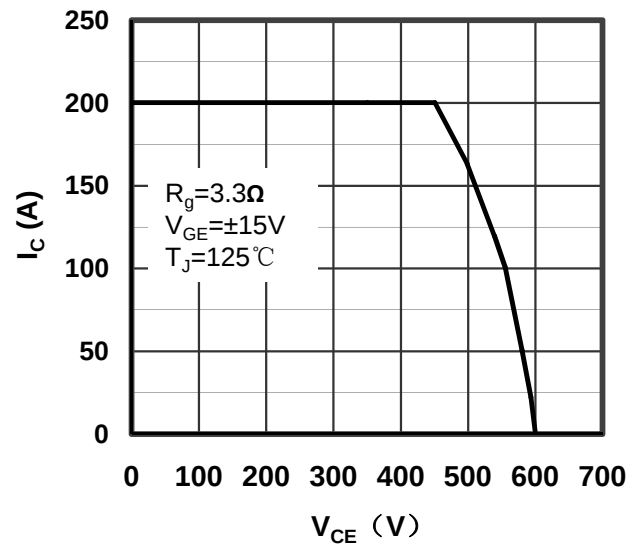


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

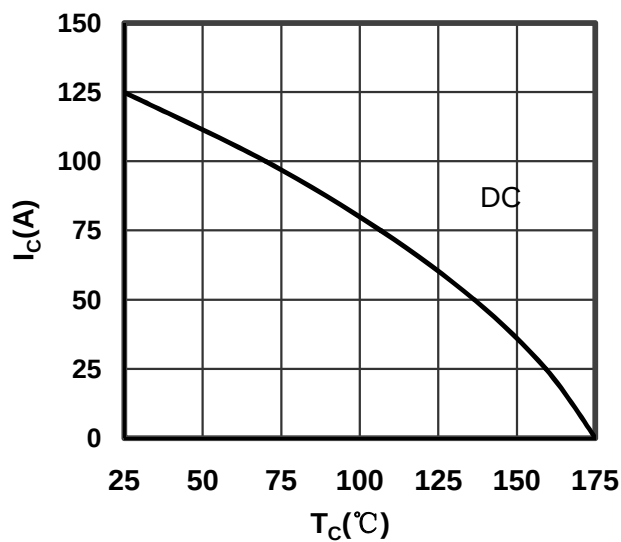


Figure 7. Collector Current vs Case temperature IGBT -inverter

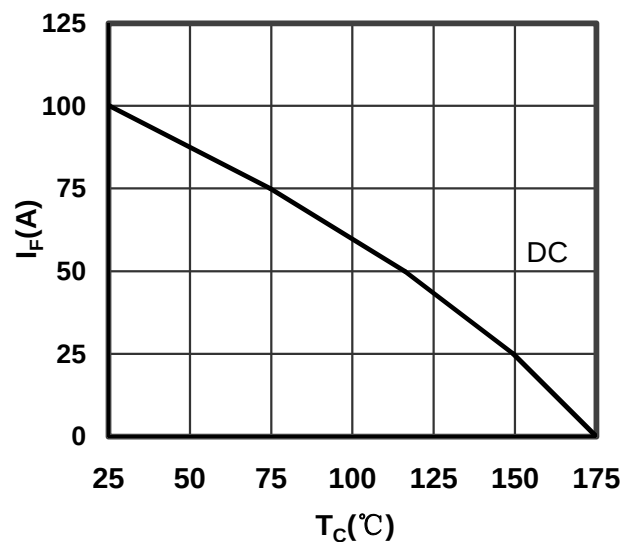


Figure 8. Forward current vs Case temperature Diode -inverter

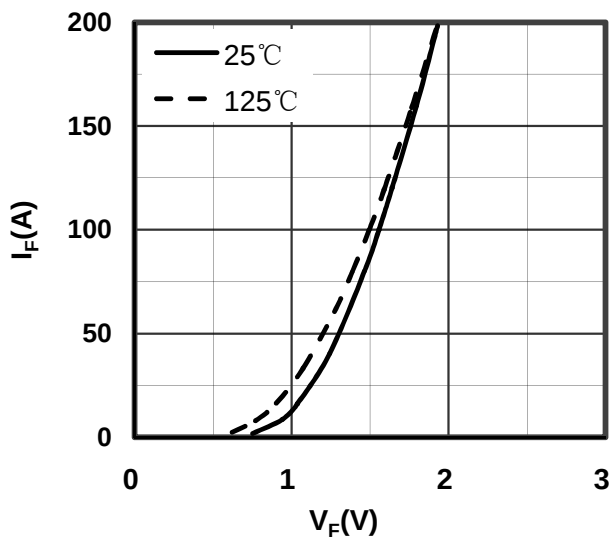


Figure 9. Diode Forward Characteristics Diode -inverter

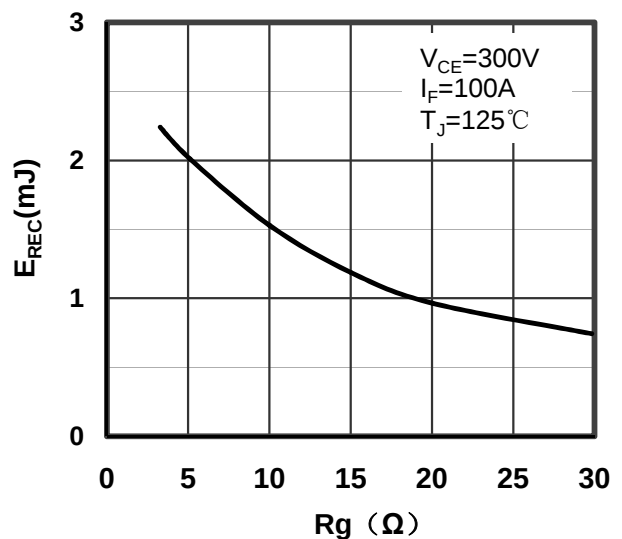


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

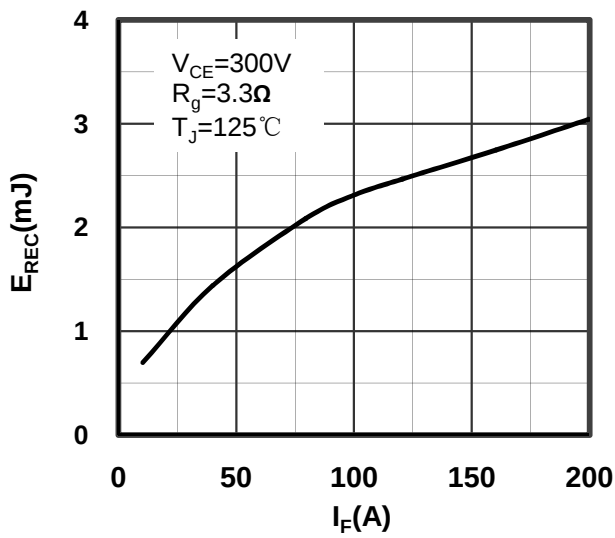


Figure 11. Switching Energy vs Forward Current Diode-inverter

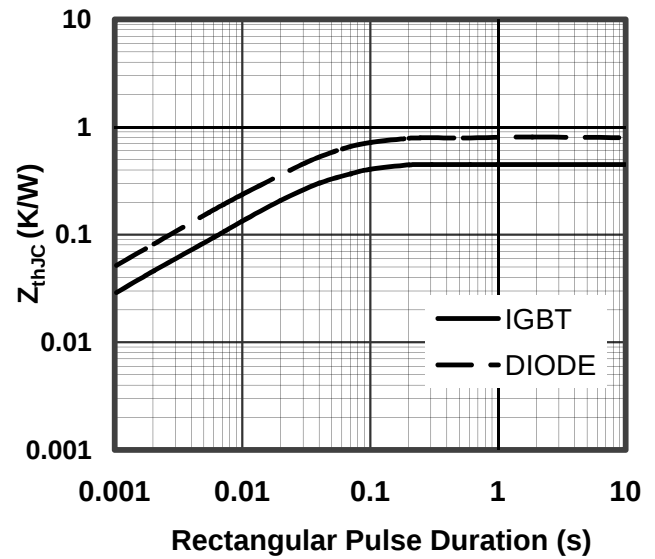


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

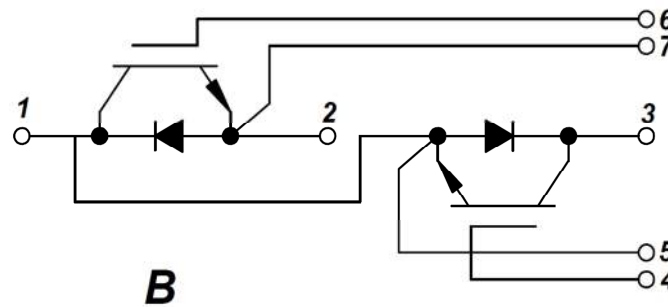
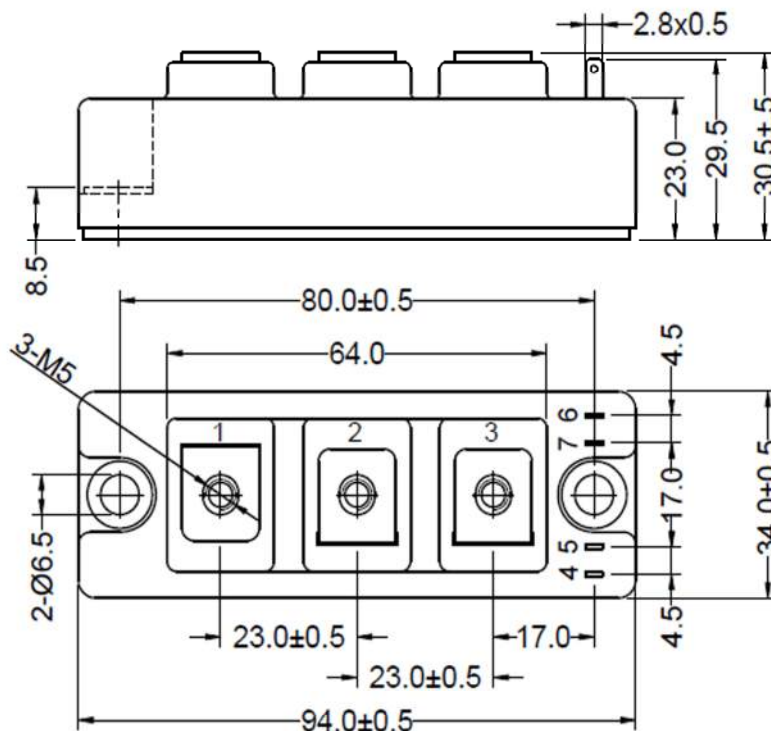


Figure 13. Circuit Diagram



Dimensions in (mm)
Figure 14. Package Outline